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APPLICATION NO). F	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/009,910		12/12/2001	Makoto Iida	81839.0107	7347	
26021	7590	08/21/2003				
		SON L.L.P.	EXAMINER .			
500 S. GRAND AVENUE SUITE 1900				SONG, MA	SONG, MATTHEW J	
LOS ANG	ELES, CA	90071-2611		ART UNIT PAPER NUMBER		
				1765		
				DATE MAILED: 08/21/2003	DATE MAILED: 08/21/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

			41
	Application No.	Applicant(s)	
Advisory Action	10/009,910	IIDA ET AL.	
•	Examiner	Art Unit	
	Matthew J Song	1765	
The MAILING DATE of this communication appe	ars on the cover sheet with the c	orrespondence add	ress
THE REPLY FILED FAILS TO PLACE THIS APF Therefore, further action by the applicant is required to a final rejection under 37 CFR 1.113 may only be either: ('condition for allowance; (2) a timely filed Notice of Appe Examination (RCE) in compliance with 37 CFR 1.114.	 a timely filed amendment whi 	cation. A proper rech places the application	cation in
PERIOD FOR RE	PLY [check either a) or b)]		
a) The period for reply expires 3 months from the mailing date of b) The period for reply expires on: (1) the mailing date of this Advevent, however, will the statutory period for reply expire later the ONLY CHECK THIS BOX WHEN THE FIRST REPLY WAS 706.07(f). Extensions of time may be obtained under 37 CFR 1.136(a). The date of the period for reply expire later than the period for reply expires and the period for reply expires and the period for reply expires and the period for reply expires on: (1) the mailing date of the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires and the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the mailing date of this Adversariant than the period for reply expires on: (1) the period for reply expires on: (isory Action, or (2) the date set forth in the an SIX MONTHS from the mailing date of FILED WITHIN TWO MONTHS OF THE	f the final rejection. E FINAL REJECTION. \$	See MPEP
have been filed is the date for purposes of determining the period of extensions of the shortened from: (1) the expiration date of the shortened (b) above, if checked. Any reply received by the Office later than three mo	sion and the corresponding amount of the statutory period for reply originally set in	fee. The appropriate extending of the final Office action; or	tension fee under (2) as set forth in
1. A Notice of Appeal was filed on Appellant's 37 CFR 1.192(a), or any extension thereof (37 CFR	s Brief must be filed within the p R 1.191(d)), to avoid dismissal (period set forth in of the appeal.	
2. The proposed amendment(s) will not be entered be	ecause:		
(a) they raise new issues that would require further	er consideration and/or search (see NOTE below);	
(b) they raise the issue of new matter (see Note b	pelow);		
(c) they are not deemed to place the application i issues for appeal; and/or	n better form for appeal by mate	erially reducing or s	simplifying the
(d) they present additional claims without cancel NOTE:	ing a corresponding number of f	finally rejected clair	ns.
3. Applicant's reply has overcome the following rejection	tion(s):		
4. Newly proposed or amended claim(s) would canceling the non-allowable claim(s).	be allowable if submitted in a s	eparate, timely filed	d amendment
 5. ☐ The a) ☐ affidavit, b) ☐ exhibit, or c) ☐ req place the application in condition for allow 6. ☐ The affidavit or exhibit will NOT be considered becaused by the Examiner in the final rejection. 	ance because: See Continuation	<u>Sheet</u> .	
7. For purposes of Appeal, the proposed amendment explanation of how the new or amended claims we	r(s) a)⊠ will not be entered or b ould be rejected is provided belo)□ will be entered ow or appended.	and an
The status of the claim(s) is (or will be) as follows:			
Claim(s) allowed:			
Claim(s) objected to:			
Claim(s) rejected: 1-18.			
Claim(s) withdrawn from consideration:			
8. The proposed drawing correction filed on is	a) approved or b) disapp	proved by the Exam	niner.
9. Note the attached Information Disclosure Statemen			
10. Other:		NADINE'G. NO PRIMARY EXA	RTON MINER
		11/1/1	,

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Response to Arguments

Applicant's arguments filed 8/11/2003 have been fully considered but they are not persuasive.

In response to applicant's arguments against the references individually, one cannot show nonobviousness by attacking references individually where the rejections are based on combinations of references. See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981); *In re Merck & Co.*, 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986). Iida is relied upon solely as a teaching of forming an N region over an entire plane of a crystal. Fujikawa is relied upon as a teaching of doping a silicon single crystal with carbon. The combination of Iida and Fujikawa teach all of the limitations of claim 1.

In response to applicant's argument that the examiner's conclusion of obviousness is based upon improper hindsight reasoning, it must be recognized that any judgment on obviousness is in a sense necessarily a reconstruction based upon hindsight reasoning. But so long as it takes into account only knowledge which was within the level of ordinary skill at the time the claimed invention was made, and does not include knowledge gleaned only from the applicant's disclosure, such a reconstruction is proper. See *In re McLaughlin*, 443 F.2d 1392, 170 USPQ 209 (CCPA 1971). Fujikawa teaches an advantage to doping a silicon single crystal with carbon; the advantage being a larger achievable oxygen precipitation fostering effect, note column 6, lines 59-63.

In response to applicant's argument that the single crystal having the N-region can be pulled faster than a single crystal in the case of not doping with carbon, the fact that applicant has recognized another advantage which would flow naturally from following the suggestion of

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the prior art cannot be the basis for patentability when the differences would otherwise be obvious. See *Ex parte Obiaya*, 227 USPQ 58, 60 (Bd. Pat. App. & Inter. 1985). The combination of Iida and Fujikawa teach doping a silicon single crystal with carbon and forming a N region over the entire cross section of a crystal by controlling the pulling rate and temperature gradient; therefore increasing the pulling rate would flow naturally from the suggestion of the prior to dope the single crystal with carbon.

In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies (i.e., compensation of the weak point of doping nitrogen by doping with carbon to obtain a synergistic effect (pg 8)) are not recited in the rejected claim(s). Although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

Applicant's argument that the idea of doping a N-region crystal with carbon cannot be derived has been considered but is not found persuasive. Fujikawa teaches doping a silicon single crystal with 0.5 ppma of carbon, which overlaps the concentration of 0.1 ppma or more taught by applicant, note page 9, lines 5-6 of the instant specification. Iida et al teach forming an N-region over the entire region of silicon single crystal by controlling the temperature gradient, G, and the pulling rate, V. Therefore, it would have been obvious to a person of ordinary skill in the art at the time of the invention that pulling rate can be optimized to obtain a N-region crystal.

In response to applicant's argument that there is no suggestion to combine the references, the examiner recognizes that obviousness can only be established by combining or modifying the teachings of the prior art to produce the claimed invention where there is some teaching,

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suggestion, or motivation to do so found either in the references themselves or in the knowledge generally available to one of ordinary skill in the art. See *In re Fine*, 837 F.2d 1071, 5

USPQ2d 1596 (Fed. Cir. 1988) and *In re Jones*, 958 F.2d 347, 21 USPQ2d 1941 (Fed. Cir. 1992). In this case, Fujikawa teaches an advantage to doping a silicon single crystal with carbon; the advantage being a larger achievable oxygen precipitation fostering effect, note column 6, lines 59-63.

Applicant's argument the cited references do not teach the specific concentration ranges of each impurity are combined is noted but is not found persuasive.

In response to applicant's arguments against the references individually, one cannot show nonobviousness by attacking references individually where the rejections are based on combinations of references. See *In re Keller*, 642 F.2d 413, 208 USPQ 871 (CCPA 1981); *In re Merck & Co.*, 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986). It is noted that specific concentration ranges of each impurity are not taught in a single reference. However, Fujikawa teaches a carbon concentration, which overlaps the claimed concentration and Tamatsuka teaches the nitrogen and oxygen concentrations, which overlaps the claimed concentration; therefore reads on the instant claims. Furthermore, the selection of reaction parameters such as temperature and concentration is obvious (In re Aller 105 USPQ 233, 255 (CCPA 1955)).

In response to applicant's argument that the references fail to show certain features of applicant's invention, it is noted that the features upon which applicant relies (i.e., the specific concentration ranges of each impurity are combined to prevent the generation of secondary defects) are not recited in the rejected claim(s). Although the claims are interpreted in light of

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the specification, limitations from the specification are not read into the claims. See In re Van

Geuns, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

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